Features

- Trench Power LV MOSFET Technology
- Excellent Package for Heat Dissipation
- High Density Cell Design for Low $R_{DS(ON)}$
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Moisture Sensitivity Level 1

P-CHANNEL MOSFET

Maximum Ratings

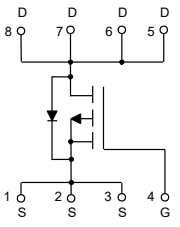
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 3.3°C/W Junction to Case(2)
- Thermal Resistance: 150°C/W Junction to Ambient(2)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Volltage	V_{GS}	±20	V
Continuous Drain Current	I_D	-35	A
Pulsed Drain Current(3)	I_{DM}	-140	A
Total Power Dissipation	P_D	38	W
Single Pulsed Avalanche Energy(4)	E_{AS}	50	mJ

Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The Value of $R_{\theta JA}$ is Measured with the Device Mounted on 1in2 FR-4 Board with 2oz. Copper, in a Still Air Environment with T_A=25°C. The Value in Any Given Application Depends on the User's Specific Board Design.
   the Value of $R_{\theta JC}$ is Measured with Surface Mounted on 1 in^2 pad area, t≤10 sec.
3. Pulse Test: Pulse Width≤300us,Duty cycle ≤2%.
4. V_{DS}=-35V, V_{GS}=-10V, L=1mH.
5. For design aid only, not subject to production testing.

Internal Structure and Marking Code



pin1

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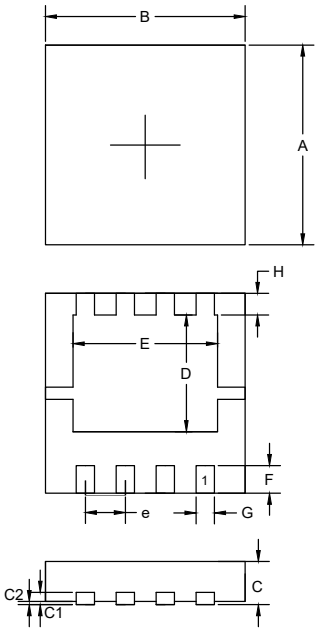


DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.126	0.130	3.20	3.30	
B	0.126	0.130	3.20	3.30	
C	0.030	0.033	0.75	0.85	
C1	0.007	0.009	0.18	0.22	
C2	---	0.002	---	0.05	
D	0.071	0.079	1.80	2.00	
E	0.087	0.098	2.20	2.50	
F	0.016	0.020	0.40	0.50	
G	0.010	0.014	0.25	0.35	
H	0.012	0.016	0.30	0.40	
e	0.024	0.028	0.60	0.70	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=-250μA	-40			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-40V, V_{GS}=0V			-1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-1	-1.7	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V, I_D=-15A		17	25	mΩ
		V_{GS}=-4.5V, I_D=-10A		25	35	mΩ
Forward Transconductance (3)(5)	gfs	V_{DS}=-5V, I_D=-1A		5.5		S
Diode Characteristics						
Continuous Body Diode Current	I_S				-35	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-20A			-1.3	V
Reverse Recovery Time	t_{rr}	I_F=-12A, dI_F/dt=100A/μs		21.5		ns
Reverse Recovery Charge	Q_{rr}			5		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=-20V,V_{GS}=0V,f=1MHz		1257		pF
Output Capacitance	C_{oss}			129		
Reverse Transfer Capacitance	C_{rss}			110		
Total Gate Charge	Q_g	V_{DS}=-20V,V_{GS}=-10V,I_D=-3A		26.6		nC
Gate-Source Charge	Q_{gs}			5.1		
Gate-Drain Charge	Q_{gd}			4.6		
Turn-On Delay Time	$t_{d(on)}$	V_{DS}=-20V, V_{GS}=-10V, R_G=3.3Ω, I_{DS}=-3A		5.4		ns
Turn-On Rise Time	t_r			21.5		
Turn-Off Delay Time	$t_{d(off)}$			94.7		
Turn-Off Fall Time	t_f			45.2		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

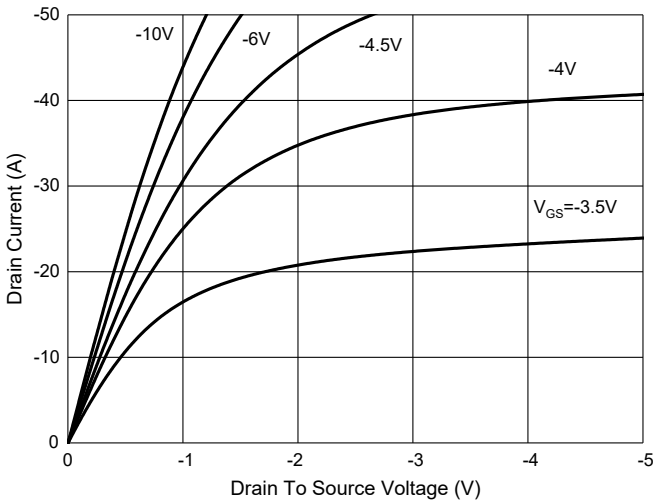


Fig. 2 - Transfer Characteristics

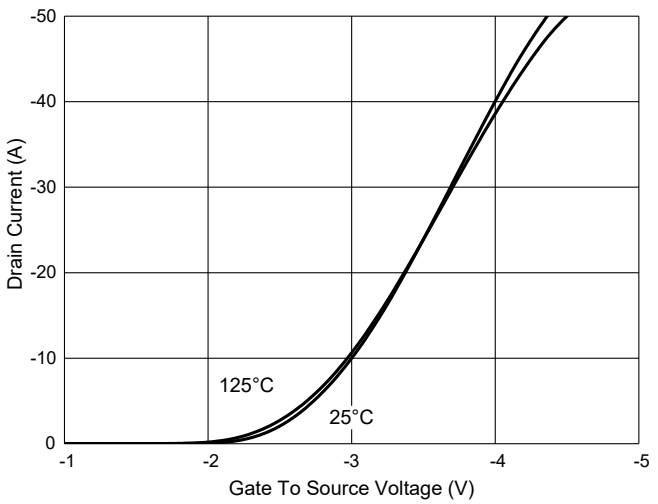


Fig. 3 - $R_{DS(ON)}$—I_D

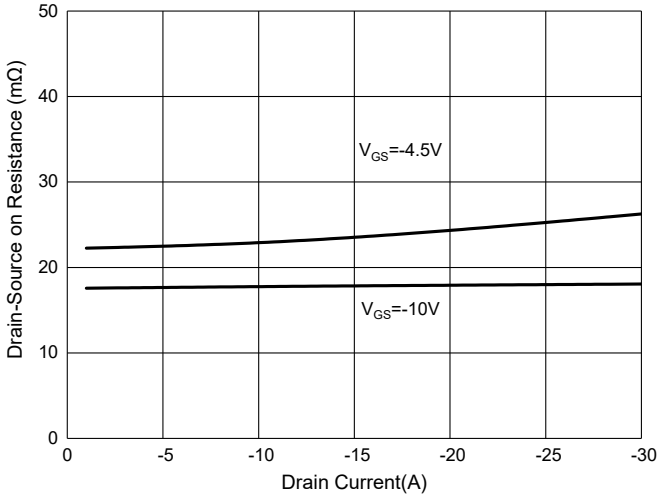


Fig. 4 - Normalized On Resistance Characteristics

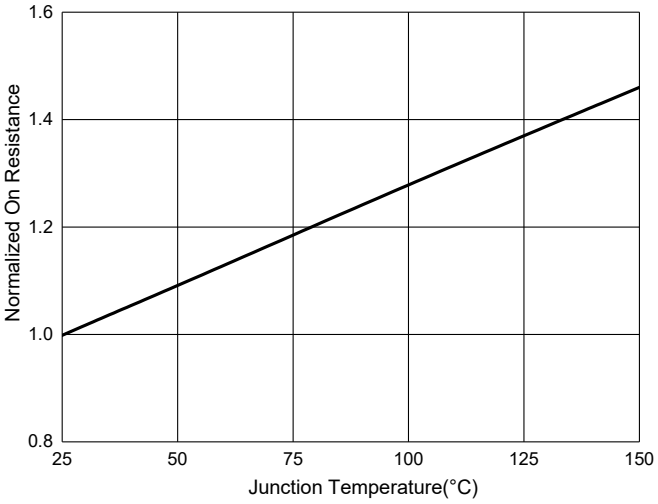


Fig. 5 - Capacitance Characteristics

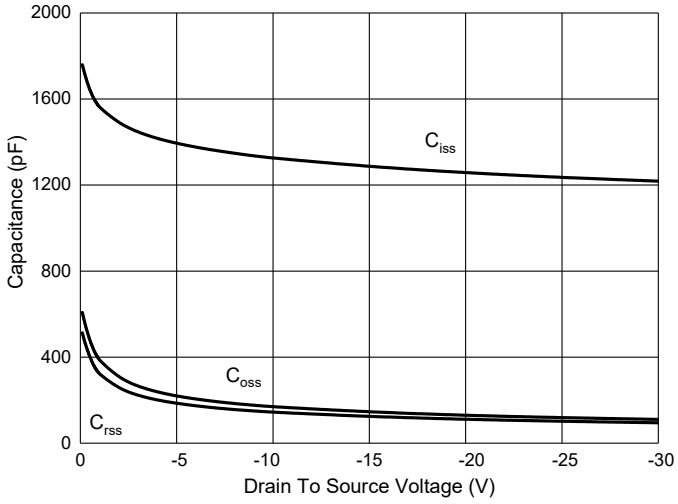
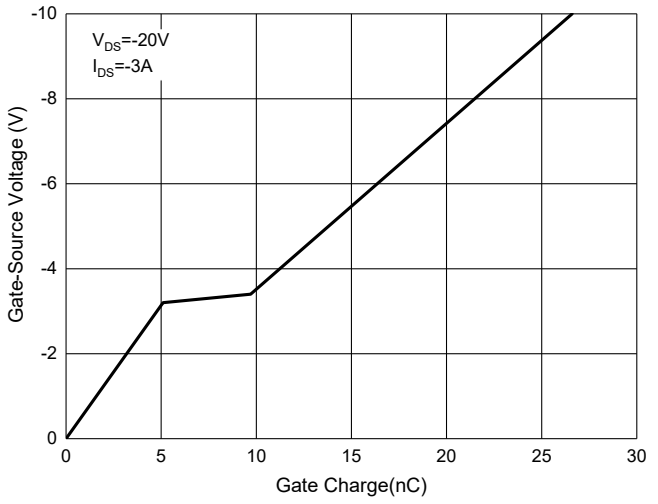


Fig. 6 - Gate Charge



Curve Characteristics

Fig. 7 - Safe Operation Area

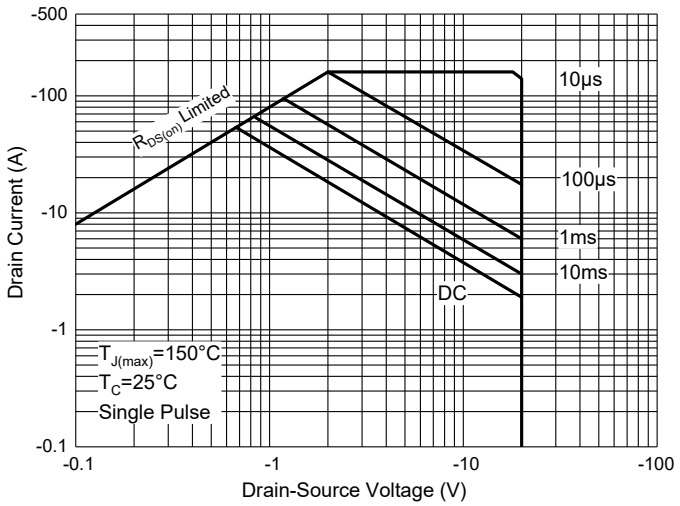
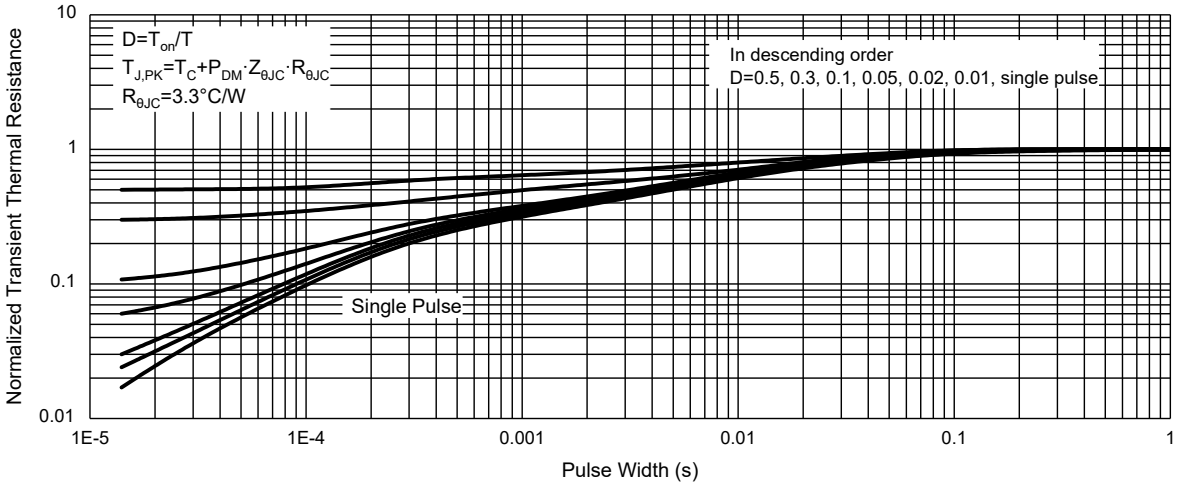


Fig. 8 - Normalized Maximum Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel